

## NTE575 General Purpose Silicon Rectifier Fast Recovery

**Features:**

- Low Switching Noise
- Low Forward Voltage Drop
- Low Thermal Resistance
- High Current Capability
- High Switching Capability
- High Surge Capability
- High Reliability

**Maximum Ratings and Electrical Characteristics:**

( $T_A = +25^\circ\text{C}$  unless otherwise specified. Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%)

Maximum Recurrent Peak Reverse Voltage, $V_{RRM}$ .....	1000V
Maximum RMS Voltage, $V_{RMS}$ .....	700V
Maximum DC Blocking Voltage, $V_{DC}$ .....	1000V
Maximum Average Forward Rectified Output Current ( $T_A = +55^\circ\text{C}$ ), $I_{(AV)}$ .....	1A
Peak Forward Surge Current, $I_{FSM}$ (8.3ms single half sine wave superimposed on rated load) .....	35A
Maximum Instantaneous Forward Voltage (At 1A), $V_F$ .....	1.5V
Maximum DC Reverse Current ( $V_{DC} = 1000\text{V}$ ), $I_R$ .....	50 $\mu\text{A}$
Maximum Reverse Recovery Time ( $I_F = 0.5\text{A}$ , $I_R = 1\text{A}$ , $I_{RR} = 0.25\text{A}$ ), $t_{rr}$ .....	70ns
Typical Junction Capacitance (Note 1), $C_J$ .....	15pF
Thermal Resistance, Junction-to-Air ( $^{\circ}\text{W}/\text{fin}$ ), $R_{thJA}$ .....	50 $^{\circ}\text{C}/\text{W}$
Operating Junction Temperature Range, $T_J$ .....	-65 $^{\circ}$ to +150 $^{\circ}\text{C}$
Storage Temperature Range, $T_{stg}$ .....	-65 $^{\circ}$ to +150 $^{\circ}\text{C}$

Note 1. Measured at 1MHz and applied reverse voltage of 4V.

